

Discription

The ESD11LL5.0CT5G is designed to protect voltage sensitive components from ESD. Excellent clamping capability, low leakage, and fast response time, make these parts ideal for ESD protection on designs where board space is at a premium. Because of its small size, it is suited for use in cellular phones, digital cameras and many other portable applications where board space is at a premium.

Applications

- I Cellular phones audio
- I Digital cameras
- I Portable applications
- I Mobile telephone

Features

- Small Body Outline Dimensions: 0.61 mm x 0.31 mm
- I Low Body Height: 0.28 mm
- | Low Leakage
- I Response Time is Typically < 1 ns
- I ESD Rating of Class 3 per Human Body Model
- IEC61000-4-2 Level 4 ESD Protection
- These are Pb-Free Devices
- I We declare that the material of product compliance with RoHS requirements and Halogen Free.



DFN0603-DL





Q =Specific Device Code M = Month Code

Ordering information

Device	Marking	Shipping	
ESD11LL5.0CT5G	Q	15000/Tape&Reel	

MAXIMUM RATINGS

Rating	Symbol	Value	Unit		
IEC 61000-4-2 (ESD) Air discharge		±20	kV		
Contact discharge		±16	kV		
Total Power Dissipation on FR-5 Board (Note 1)	PD	200	mW		
@ T _A =25℃					
Junction and Storage Temperature Range	TJ,TSTG	-55 to 150	${\mathbb C}$		
Lead Solder Temperature – Maximum (10	TL	260	$^{\circ}$		
Second Duration)					

Stresses exceeding Maximum Ratings may damage the device. Maximum Rating are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

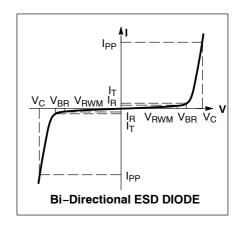
1. FR-5 = 1.0*0.75*0.62 in.



ELECTRICAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

Symbol	Parameter		
I _{PP}	I _{PP} Maximum Reverse Peak Pulse Current		
V _C	Clamping Voltage @ I _{PP}		
V_{RWM}	Working Peak Reverse Voltage		
I _R	Maximum Reverse Leakage Current @ V _{RWM}		
V _{BR} Breakdown Voltage @ I _T			
Ι _Τ	Test Current		
P _{pk}	Peak Power Dissipation		
С	Capacitance @ V _R = 0 and f = 1.0 MHz		

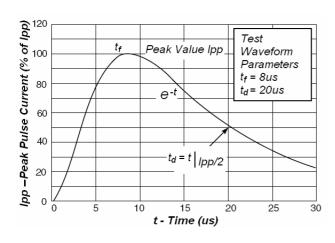


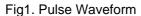
ELECTRICAL CHARACTERISTICS

	V_{RWM}	I_R	V _B		I _T	I _{PP}	V _C	P _{PK}	С
	(V)	(µ A)	(V)	(mA)	(A)	(V)	(W)	(pF)
Device		@	@	lτ			@ Max I _{PP}	(8*20 µs)	
501.00		V_{RWM}	(Note	e 1)					
	Max	Max	Min	Max		Max	Max	Max	Max
LESD11LL5.0CT5G	5.0	0.5	6	8.8	1.0	4	20	80	0.3

Other voltage available upon request.

- 2. V_{BR} is measured with a pulse test current IT at an ambient temperature of 25 $^{\circ}\mathrm{C}$
- 3. Surge current waveform per Figure 1.





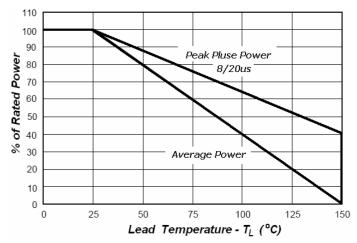


Fig2.Power Derating Curve





Fig3. ESD Clamping Voltage Screenshot Positive 8 kV Contact per IEC61000-4-2

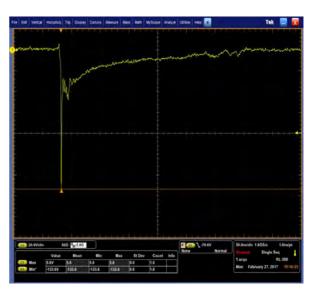


Fig4. ESD Clamping Voltage Screenshot Negative 8 kV Contact per IEC61000-4-2

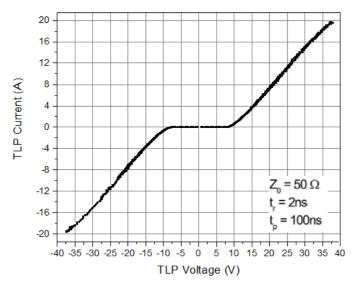
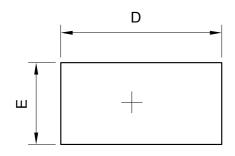
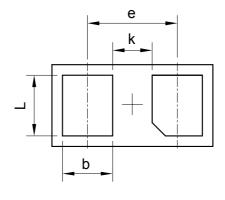


Fig5.TLP Measurement



OUTLINE AND DIMENSIONS





TOP VIEW

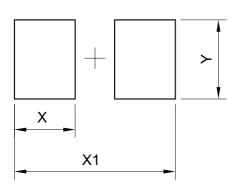
BOTTOM VIEW

DFN0603-DL				
Dim	Min	Min Typ. M		
D	0.58	0.61	0.64	
Е	0.28	0.28 0.31		
е	1	0.34	-	
Ш	0.20	0.23	0.26	
b	0.16 0.19		0.22	
Α	0.25 0.28		0.31	
k	0.12	0.15	0.18	
All Dimensions in mm				



SIDE VIEW

SOLDERING FOOTPRINT



DFN0603-DL					
DIM (mm)					
Χ	0.23				
X1	0.61				
Υ	0.30				